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Siliup Semiconductor

SP60N13P8

60V Uni N-Channel MOSFET

Product Summary

$V_{(BR)DSS}$	$R_{DS(on)TYP}$	I_D
60V	13mΩ@10V	9A
	18mΩ@4.5V	

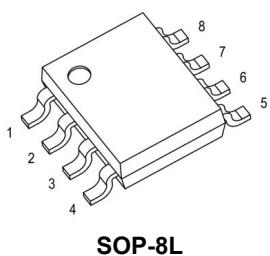
Feature

- High density cell design for ultra low Rdson
- Fully characterized avalanche voltage and current
- Low gate to drain charge to reduce switching losses

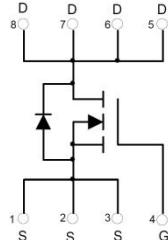
Application

- Power switching application
- Load switch

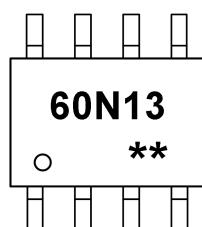
Package



Circuit diagram



Marking



60N13 : Product code
** : Week code.



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Absolute maximum ratings (Ta=25°C unless otherwise noted)

Parameter	Symbol	Limit	Unit
Drain-Source Voltage	V _{DS}	60	V
Gate-Source Voltage	V _{GS}	±20	V
Drain Current-Continuous	I _D	9	A
Pulsed Drain Current ⁽¹⁾	I _{DM}	36	A
Maximum Power Dissipation	P _D	2.1	W
Thermal Resistance, Junction-to-Case ⁽²⁾	R _{θJC}	60	°C/W
Operating Junction and Storage Temperature Range	T _J , T _{STG}	-55 To 150	°C

Electrical characteristics (T_A=25 °C, unless otherwise noted)

Characteristic	Symbol	Test Condition	Min	Typ	Max	Unit
Static Electrical Characteristics						
Drain-Source Breakdown Voltage	BV _{DSS}	V _{GS} = 0V, ID = 250µA	60			V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 60V, V _{GS} = 0V			1	µA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±20V, V _{DS} = 0V			±100	nA
Gate Threshold Voltage	V _{GS(TH)}	V _{DS} = V _{GS} , ID = 250µA	1	1.6	2.5	V
Static Drain-Source On-Resistance	R _{DS(ON)}	V _{GS} = 10V, ID = 10A		13	18	mΩ
		V _{GS} = 4.5V, ID = 6A		18	26	
Dynamic Characteristics						
Input Capacitance	C _{iss}	V _{DS} = 30V, V _{GS} = 0V, f = 1MHz		2750		pF
Output Capacitance	C _{oss}			170		
Reverse Transfer Capacitance	C _{rss}			150		
Total Gate Charge	Q _g	V _{DS} = 30V, ID = 10A		60		nC
Gate-Source Charge	Q _{gs}			10		
Gate-Drain Charge	Q _{gd}			14		
Switching Characteristics						
Turn-On Delay Time	t _{D(ON)}	V _{GS} = 10V, V _{DS} = 30V, RG = 6Ω, ID = 10A		9		ns
Turn-On Rise Time	t _R			7		
Turn-Off Delay Time	t _{D(OFF)}			33		
Turn-Off Fall Time	t _F			7		
Drain-Source Diode Characteristics						
Diode Forward Voltage	V _{SD}	V _{GS} = 0V, IS = 1A		0.7	1.2	V
Reverse Recovery Time	t _{RR}	IF = 10A, di/dt = 100A/µs		22		ns
Reverse Recovery Charge	Q _{RR}			11		nC



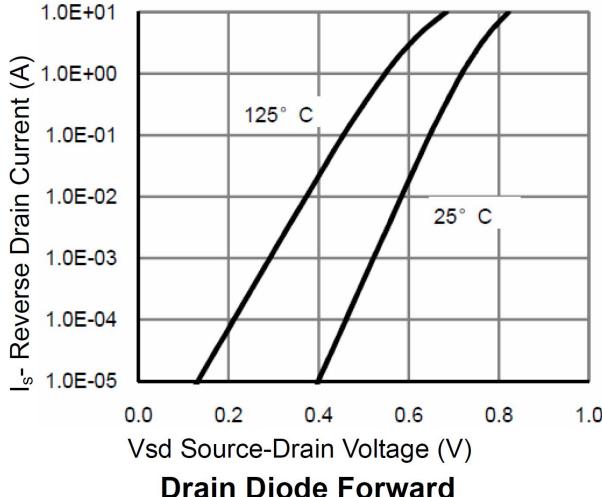
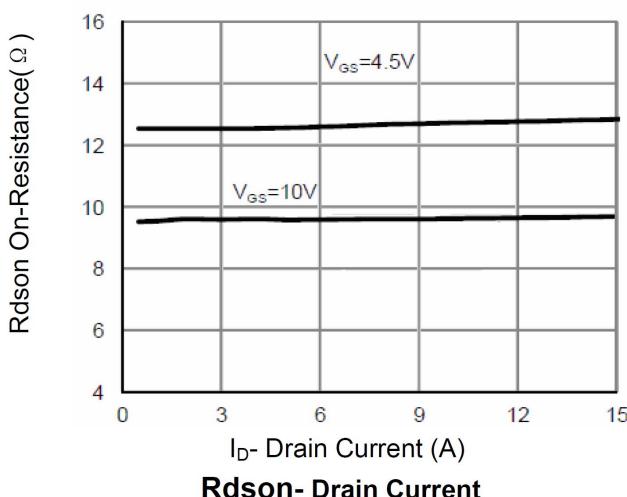
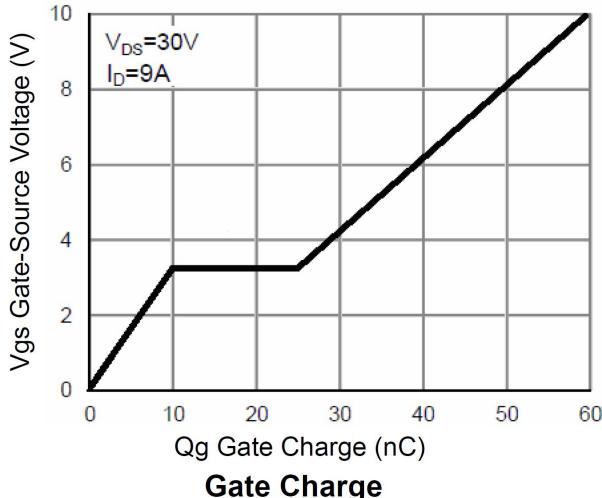
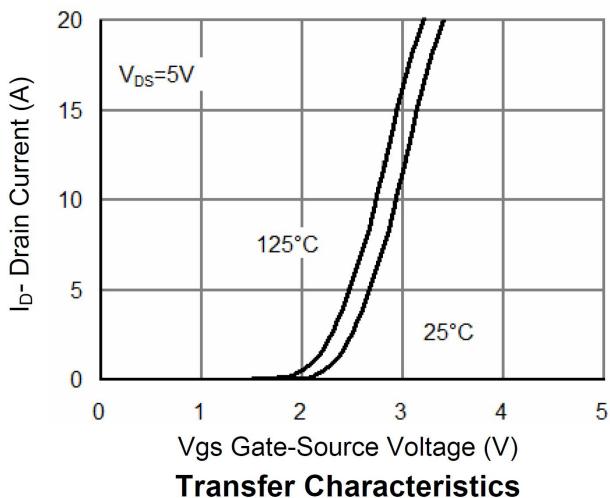
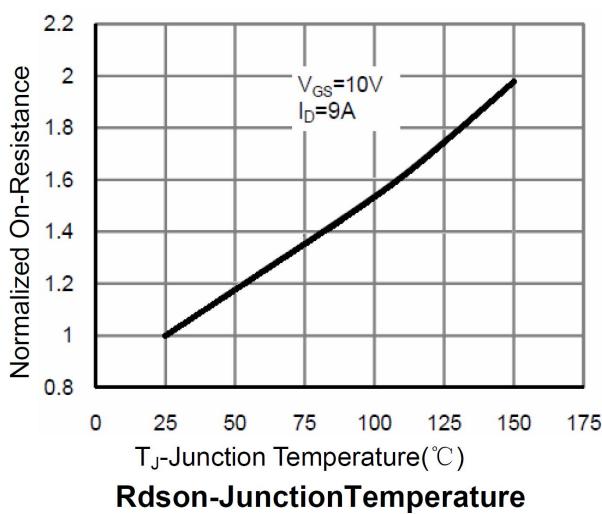
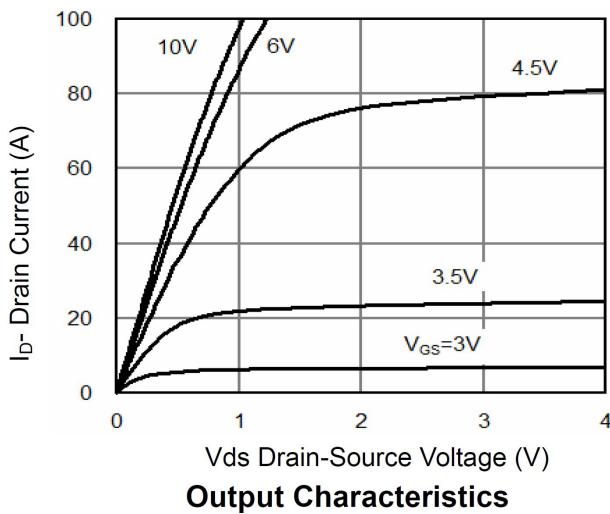
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Typical Characteristics



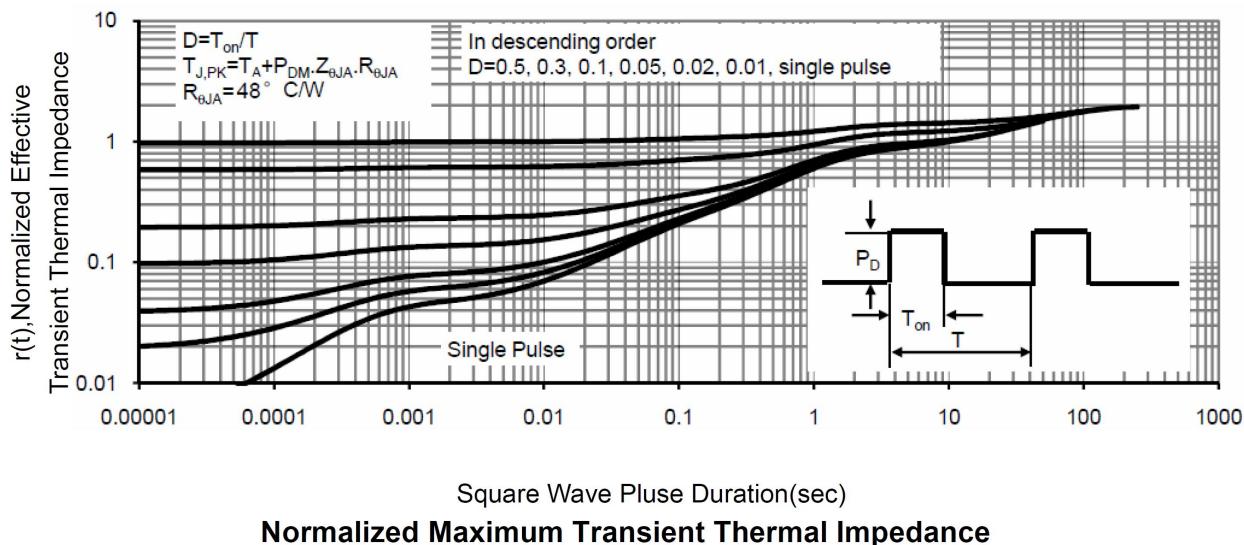
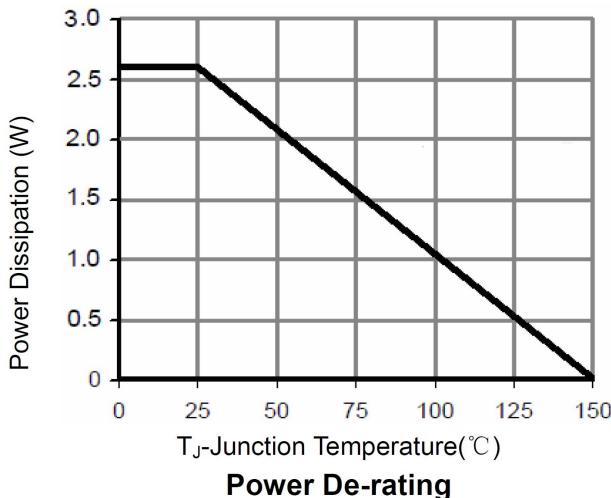
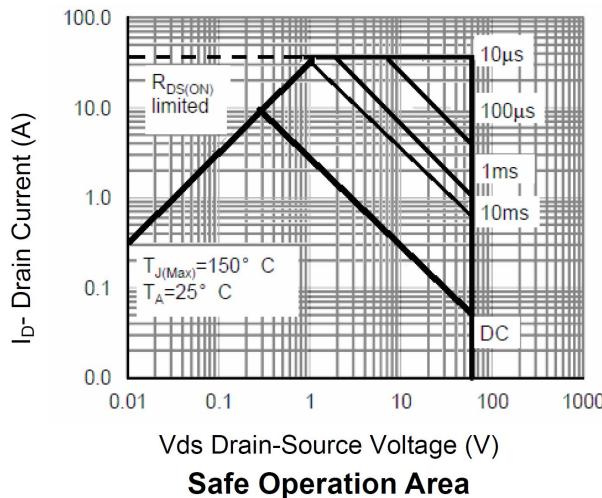
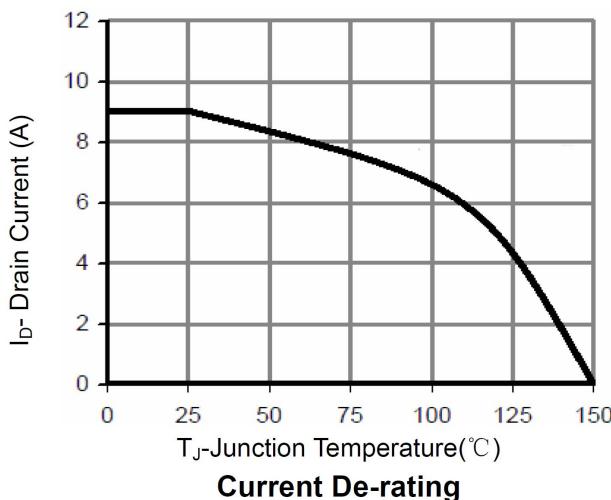
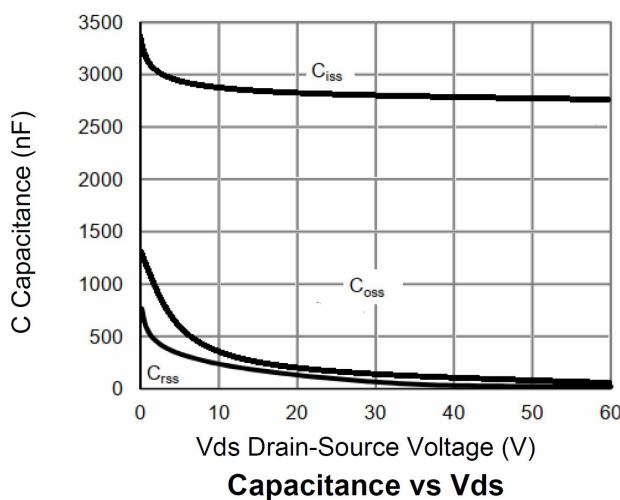


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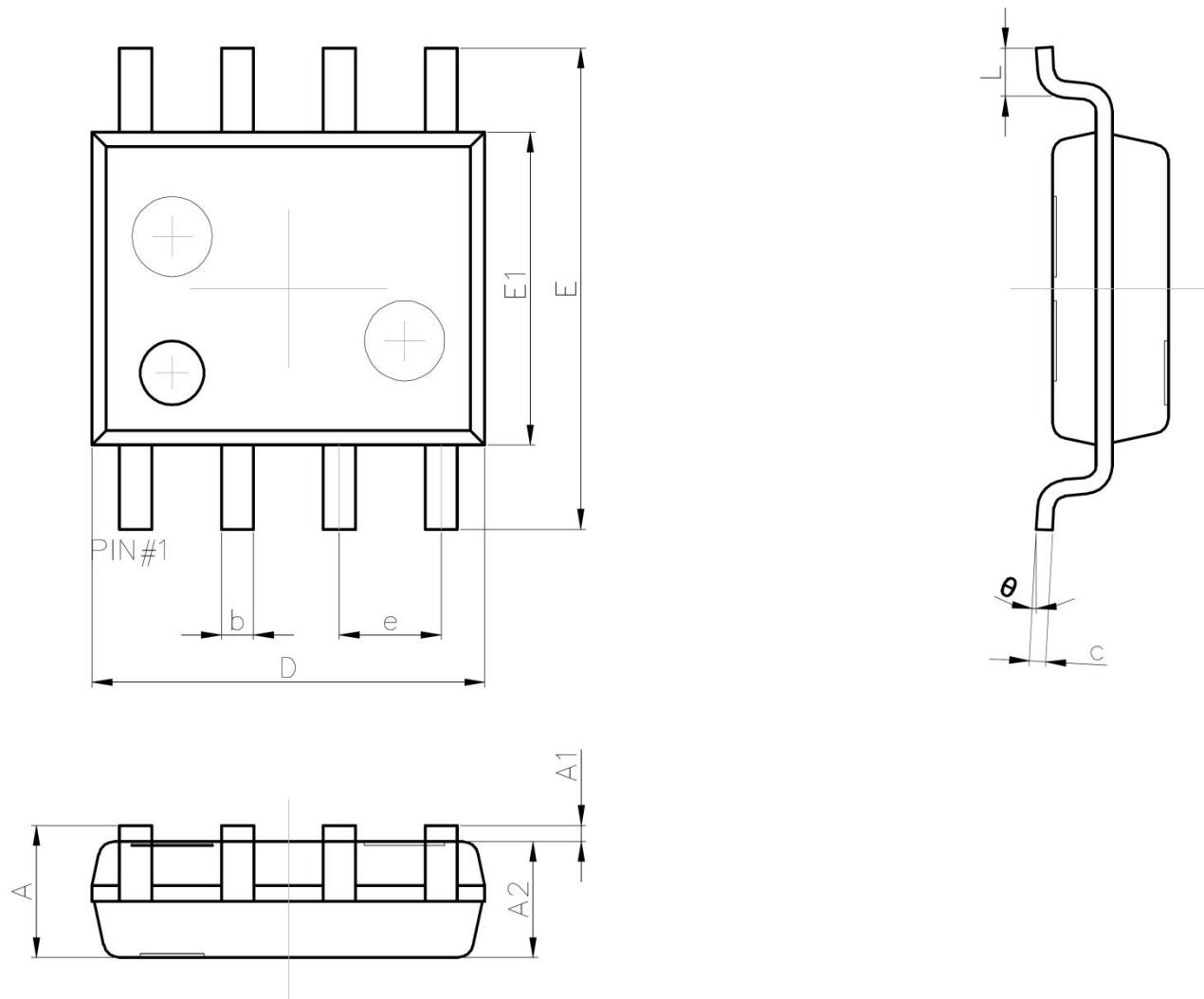
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SOP-8L Package Information



Symbol	Dimensions In Millimeters	
	Min.	Max.
A	1.35	1.75
A1	0.10	0.25
A2	1.35	1.55
b	0.33	0.51
c	0.17	0.25
D	4.80	5.00
e	1.27 REF.	
E	5.80	6.20
E1	3.80	4.00
L	0.40	1.27
θ	0°	8°